UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO.

: 7.105,208 B2

Page 1 of 1

APPLICATION NO.: 10/699013

DATED

: September 12, 2006

INVENTOR(S)

: Craig M. Carpenter

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col. 1, line 24 –

Replace "deposition (CVD) and atomic layer deposition (CVD). CVD" With --deposition (CVD) and atomic layer deposition (ALD). CVD--

Col. 3, line 10 -

Replace "in the periodic table, namely, Al, Ga, In, TI, Ge, Sn, Pb, Sb," With -- in the periodic table, namely, Al, Ga, In, Tl, Ge, Sn, Pb, Sb,--

Col. 3, line 64 –

Replace "forming other than One monolayer at a time by stacking of" With -- forming other than one monolayer at a time by stacking of --

Col. 4, line 7 –

Replace "Traditional ALD can occur within an frequently-used" With -- Traditional ALD can occur within frequently-used --

Col. 4, line 23 -

Replace "CVD is commonly used to form non-selectively a complete," With --CVD is commonly used to form non-selectively complete,--

Signed and Sealed this

Twenty-fourth Day of July, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office